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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/710,608	07/23/2004	Kangguo Cheng		4607
	7590 10/16/2007		EXAMINER	
MCGUIRE WOODS LLP 1750 TYSONS BLVD. SUITE 1800 MCLEAN, VA 22102-4215			REAMES, MATTHEW L	
			ART UNIT	PAPER NUMBER
		·	2891	· · · · · · · · · · · · · · · · · · ·
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		•	MAIL DATE	DELIVERY MODE
	•		10/16/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)
Office Action Summary		10/710,608	CHENG ET AL.
		Examiner	Art Unit
		Matthew L. Reames	2891
Pariod fe	- The MAILING DATE of this communication ap	ppears on the cover sheet w	
A SHOWHICE - Externafter - If NO - Failur Any rearns Status 1) 2a) 3 Dispositi 4) 3 5) 6 6) 6 7) 7	ORTENED STATUTORY PERIOD FOR REPLECHEVER IS LONGER, FROM THE MAILING Ensions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. Operiod for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statuted part of the provisions of 37 CFR 1. To a period for reply will, by statuted part of the provision of the mailing of the provision of the mailing of the provision	August 2007. Saction is non-final. Ex parte Quayle, 1935 C.E. The application. The withdrawn from considers of the consider.	MONTH(S) OR THIRTY (30) DAYS, ICATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133). It timely filed, may reduce any ters, prosecution as to the merits is D. 11, 453 O.G. 213.
Application 9) ☐ -	Claim(s) are subject to restriction and/o on Papers The specification is objected to by the Examine The drawing(s) filed on is/are: a) acc	ėr.	by the Examiner.
	Applicant may not request that any objection to the		-
	Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Extended to be the Extended to		
Priority u	nder 35 U.S.C. § 119		
a)[Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau ee the attached detailed Office action for a list	s have been received. Is have been received in A rity documents have been u (PCT Rule 17.2(a)).	pplication No received in this National Stage
Attachment((s) e of References Cited (PTO-892)	A) [] -1	·
2) Notice 3) Inform	e of References Cited (PTO-892) c of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO/SB/08) No(s)/Mail Date	Paper No(s	Summary (PTO-413) S)/Mail Date Informal Patent Application

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DETAILED ACTION

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

- 2. Claims 1 and 31 rejected under 35 U.S.C. 102(e) as being anticipated by Peterson (20030219937).
 - a. As to claims 1 and 31 Peterson teaches a patterned substrate(see fig. 1C) where in a device is formed on the strained portion and the relaxed portion (see paragraph 7).
 - b. As to claim 13 and 20, Peterson teaches a SiGe or SiGeC which can be interpreted as a doped SiGe: Ge or SiGeC: C.

Allowable Subject Matter

3. Claim 2-7 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

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Response to Arguments

4. Applicant's arguments filed 8/1/2007 have been fully considered but they are not persuasive. Applicant's argument that Peterson does not teach a strained device on the strained region and a relaxed device on the relaxed region is found not convincing since Peterson explicitly state the problem being overcome is (paragraph 7):

For example, strained and relaxed structures are used during fabrication of an integrated device in creating high-speed complementary metal-oxide semiconductor (CMOS) circuitry. Positive channel metal-oxide semiconductor (PMOS) devices with compressively strained layers (e.g. SiGe or SiGeC channels) have the desirable quality of being faster than their silicon counterparts. However, the opposite is true of compressively strained SiGe negative channel metal-oxide semiconductor (NMOS) devices; they are slower than their silicon counterparts. In order to obtain fast NMOS devices, strained Si channels are fabricated over a relaxed (e.g. SiGe or SiGeC) layer (also known as a buffer layer). The integration of both of these types of devices on a common substrate, however, requires that both strained and relaxed SiGe (or SiGeC) layers be present on that substrate. Unfortunately, current fabrication techniques do not allow the simultaneous fabrication of both strained and relaxed crystalline, poly-crystalline, and amorphous structures using common fabrication steps.

Peterson invention is as stated in his abstract:

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One embodiment of the present invention provides a system for cofabricating strained and relaxed crystalline, poly-crystalline, and
amorphous structures in an integrated circuit device using common
fabrication steps. The system operates by first receiving a substrate. The
system then fabricates multiple layers on this substrate. A layer within these
multiple layers includes both strained structures and relaxed structures. These
strained structures and relaxed structures are fabricated simultaneously using
common fabrication steps.

From the disclosure of the prior art problems and the disclosure of the Peterson invention it self evident that Peterson wanted to incorporate strained devices and relaxed devices (NMOS and PMOS) on a common substrate (see again paragraph 7).

Therefore all rejections are deemed proper and maintained.

Conclusion

5. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any

Matthew C Landey Primary Examiner 10/15/07

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extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew L. Reames whose telephone number is (571)272-2408. The examiner can normally be reached on M-Th 6:30-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, B. William Baumeister can be reached on (571)272-1722. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

MLR